

Form PTO 1449
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ATTY DOCKET NO.

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SERIAL NO.

New Application

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yasuyoshi ITOH, et al.

FILING DATE

Herewith

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,768,192	06/16/98	Boaz EITAN			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
TT	AO	2000-260887	09/22/00	Japan		
TT	AP	5-75133	03/26/93	Japan (with English extract)		X ✓
TT	AQ	2002-26149	01/25/02	Japan (with partial English translation)		X ✓
	AR					X ✓
	AS					
	AT					
	AU					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

TT	AV	Ilan BLOOM, et al., "NROM™ - A NEW NON-VOLATILE MEMORY TECHNOLOGY: FROM DEVICE TO PRODUCTS", Microelectronic Engineering 59, 2001, pgs. 213 - 223.	
TT	AW	Toshiyuki TOYOSHIMA, et al., "0.1µm LEVEL CONTACT HOLE PATTERN FORMATION WITH KrF LITHOGRAPHY BY RESOLUTION ENHANCEMENT LITHOGRAPHY ASSISTED BY CHEMICAL SHRINK (RELACS)", IEEE, IEDM, 1998, pgs. 333 - 336.	
TT	AX	J. De BLAUWE, et al., "Si-Dot NON-VOLATILE MEMORY DEVICE", Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, Tokyo, 2001, pgs. 518 - 519.	
TT	AY	Boaz EITAN, et al., "CAN NROM, A 2-BIT, TRAPPING STORAGE NVM CELL, GIVE A REAL CHALLENGE TO FLOATING GATE CELLS?", Presented at the International Conference on Solid State Devices and Materials, Tokyo, 1999, pgs. 1/3 - 3/3.	
TT	AZ	Eli LUSKY, et al., "ELECTRON DISCHARGE MODEL OF LOCALLY-TRAPPED CHARGE IN OXIDE-NITRIDE-OXIDE (ONO) GATES FOR NROM™ NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES", Presented at the Solid State Device and Materials Conference (SSDM 2001), Sep. 2001, Tokyo, Japan, pgs. 1 - 2.	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.